

74VCX163245 Low Voltage 16-Bit Dual Supply Translating Transceiver with 3-STATE Outputs

Features

- Bidirectional interface between busses ranging from 1.65V to 3.6V
- Supports Live Insertion and Withdrawal⁽¹⁾
- Static Drive (I_{OH}/I_{OL})
 - ±24mA @ 3.0V V_{CC}
 - ±18mA @ 2.3V V_{CC}
 - ±6mA @ 1.65V V_{CC}
- Uses patented Quiet Series[™] noise/EMI reduction circuitry
- Functionally compatible with 74 series 16245
- Latchup performance exceeds 300mA
- ESD performance:
 - Human Body Model >2000V
 - Machine model >200V
- Also packaged in plastic Fine-Pitch Ball Grid Array (FBGA)

Note:

 To ensure the high impedance state during power up or power down, OE_n should be tied to V_{CCB} through a pull up resistor. The minimum value of the resistor is determined by the current sourcing capability of the driver.

General Description

The VCX163245 is a dual supply, 16-bit translating transceiver that is designed for 2 way asynchronous communication between busses at different supply voltages by providing true signal translation. The supply rails consist of V_{CCA} , which is a higher potential rail operating at 2.3V to 3.6V and V_{CCB} , which is the lower potential rail operating at 1.65V to 2.7V. (V_{CCB} must be less than or equal to V_{CCA} for proper device operation). This dual supply design allows for translation from 1.8V to 2.5V busses to busses at a higher potential, up to 3.3V.

The Transmit/Receive (T/\overline{R}) input determines the direction of data flow. Transmit (active-HIGH) enables data from A Ports to B Ports; Receive (active-LOW) enables data from B Ports to A Ports. The Output Enable (\overline{OE}) input, when HIGH, disables both A and B Ports by placing them in a High-Z condition. The A Port interfaces with the higher voltage bus (2.7V to 3.3V); The B Port interfaces with the lower voltage bus (1.8V to 2.5V). Also the VCX163245 is designed so that the control pins $(T/\overline{R}_n, \overline{OE}_n)$ are supplied by V_{CCB}.

The 74VCX163245 is suitable for mixed voltage applications such as notebook computers using a 1.8V CPU and 3.3V peripheral components. It is fabricated with an Advanced CMOS technology to achieve high speed operation while maintaining low CMOS power dissipation.

Ordering Information

Order Number	Package Number	Package Description
74VCX163245G ⁽²⁾⁽³⁾	BGA54A	54-Ball Fine-Pitch Ball Grid Array (FBGA), JEDEC MO-205, 5.5mm Wide
74VCX163245MTD ⁽³⁾	MTD48	48-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 6.1mm Wide

Notes:

2. Ordering code "G" indicates Trays.

Quiet Series[™] is a trademark of Fairchild Semiconductor Corporation.

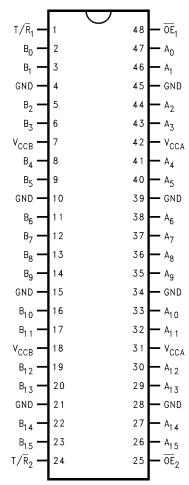
3. Device also available in Tape and Reel. Specify by appending the suffix letter "X" to the ordering code.

May 2007

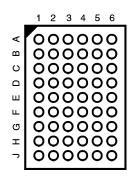
⁷⁴VCX163245 Low Voltage 16-Bit Dual Supply Translating Transceiver with 3-STATE Outputs

Connection Diagram

Pin Assignment for TSSOP



Pin Assignment for FBGA



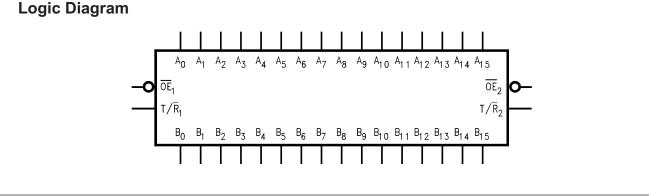
(Top Thru View)

FBGA Pin Assignments

		-	-			
	1	2	3	4	5	6
Α	B ₀	NC	T/R ₁	OE ₁	NC	A ₀
В	B ₂	B ₁	NC	NC	A ₁	A ₂
С	B ₄	B ₃	V _{CCB}	V_{CCA}	A ₃	A ₄
D	B ₆	B_5	GND	GND	A_5	A ₆
Е	B ₈	B ₇	GND	GND	A ₇	A ₈
F	B ₁₀	B ₉	GND	GND	A ₉	A ₁₀
G	B ₁₂	B ₁₁	V _{CCB}	V_{CCA}	A ₁₁	A ₁₂
Н	B ₁₄	B ₁₃	NC	NC	A ₁₃	A ₁₄
J	B ₁₅	NC	T/R ₂	\overline{OE}_2	NC	A ₁₅

Pin Descriptions

Pin Names	Description
OEn	Output Enable Input (Active LOW)
T/R _n	Transmit/Receive Input
A ₀ -A ₁₅	Side A Inputs or 3-STATE Outputs
B ₀ -B ₁₅	Side B Inputs or 3-STATE Outputs
NC	No Connect



Truth Tables

Inputs		
OE ₁ T/R ₁		Outputs
L	L	Bus B_0-B_7 Data to Bus A_0-A_7
L	Н	Bus A ₀ –A ₇ Data to Bus B ₀ –B ₇
Н	Х	HIGH Z State on A ₀ –A ₇ , B ₀ –B ₇

 Inputs
 Outputs

 OE2
 T/R2
 Outputs

 L
 L
 Bus B8-B15 Data to Bus A8-A15

 L
 H
 Bus A8-A15 Data to Bus B8-B15

 H
 X
 HIGH-Z State on A8-A15, B8-B15

H = HIGH Voltage Level

L = LOW Voltage Level

X = Immaterial (HIGH or LOW, inputs may not float)

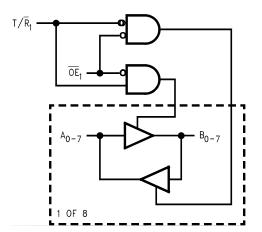
Z = High Impedance

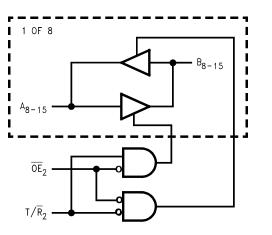
VCX163245 Translator Power Up Sequence Recommendations

To guard against power up problems, some simple guidelines need to be adhered to. The VCX163245 is designed so that the control pins (T/ \overline{R}_n , \overline{OE}_n) are supplied by V_{CCB}. Therefore the first recommendation is to begin by powering up the control side of the device, V_{CCB}. The \overline{OE}_n control pins should be ramped with or ahead of V_{CCB}, this will guard against bus contentions and oscillations as all A Port and B Port outputs will be disabled. To ensure the high impedance state during power up or power down, \overline{OE}_n should be tied to V_{CCB} through a pull up resistor. The minimum value of the resistor is determined by the current sourcing capability of the driver. Second, the T/ \overline{R}_n control pins should be

placed at logic LOW (0V) level, this will ensure that the B-side bus pins are configured as inputs to help guard against bus contention and oscillations. B-side Data Inputs should be driven to a valid logic level (0V or V_{CCB}), this will prevent excessive current draw and oscillations. V_{CCA} can then be powered up after V_{CCB} , however V_{CCA} must be greater than or equal to V_{CCB} to ensure proper device operation. Upon completion of these steps the device can then be configured for the users desired operation. Following these steps will help to prevent possible damage to the translator device as well as other system components.

Logic Diagrams





Please note that these diagrams are provided only for the understanding of logic operations and should not be used to estimate propagation delays.

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Rating
V _{CCA}	Supply Voltage	-0.5V to +4.6V
V _{CCB}		–0.5V to V _{CCA}
VI	DC Input Voltage	-0.5V to +4.6V
V _{I/O}	DC Output Voltage	
	Outputs 3-STATE	-0.5V to +4.6V
	A _n Output Active ⁽⁴⁾	–0.5V to V _{CCA} + 0.5V
	B _n Output Active ⁽⁴⁾	–0.5V to V _{CCB} + 0.5V
I _{IK}	DC Input Diode Current, V _I < 0V	–50mA
I _{OK}	DC Output Diode Current	
	V _O < 0V	–50mA
	V _O > V _{CC}	+50mA
I _{OH} /I _{OL}	DC Output Source/Sink Current	±50mA
	DC V _{CC} or Ground Current	±100mA
I _{CC} or Ground	Supply Pin	
T _{STG}	Storage Temperature	–65°C to +150°C

Recommended Operating Conditions⁽⁵⁾

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to absolute maximum ratings.

Symbol	Parameter	Rating
V _{CCA}	Power Supply ⁽⁶⁾	2.3V to 3.6V
V _{CCB}		1.65V to 2.7V
VI	Input Voltage () @ OE, T/R	0V to V _{CCB}
V _{I/O}	Input/Output Voltage ()	
	A _n	0V to V _{CCA}
	B _n	0V to V _{CCB}
I _{OH} /I _{OL}	Output Current in I _{OH} /I _{OL}	
	V _{CCA} = 3.0V to 3.6V	±24mA
	V _{CCA} = 2.3V to 2.7V	±18mA
	V _{CCB} = 2.3V to 2.7V	±18mA
	V _{CCB} = 1.65V to 1.95V	±6mA
T _A	Free Air Operating Temperature	–40°C to +85°C
$\Delta t / \Delta V$	Minimum Input Edge Rate, $V_{IN} = 0.8V$ to 2.0V, $V_{CC} = 3.0V$	10ns/V

Notes:

4. I_O Absolute Maximum Rating must be observed.

5. Unused inputs or I/O pins must be held HIGH or LOW. They may not float.

6. Operation requires: $V_{CCB} \le V_{CCA}$

Symbol	Param	eter	V _{CCB} (V)	V _{CCA} (V)	Conditions	Min.	Max.	Units
V _{IHA}	HIGH Level Input	A _n	1.65–1.95	2.3–2.7		1.6		V
V _{IHB}	Voltage	$B_n, T/\overline{R}, \overline{OE}$	1.65–1.95	2.3–2.7		0.65 x V _{CCB}		V
V _{ILA}	LOW Level Input	A _n	1.65–1.95	2.3–2.7			0.7	V
V _{ILB}	Voltage	$B_n, T/\overline{R}, \overline{OE}$	1.65–1.95	2.3–2.7			0.35 x V _{CCB}	V
V _{OHA}	HIGH Level Outpu	it Voltage	1.65–1.95	2.3–2.7	I _{OH} = -100μA	V _{CCA} -0.2		V
			1.65	2.3–2.7	I _{OH} = -18mA	1.7		
V _{OHB}	HIGH Level Outpu	it Voltage	1.65–1.95	2.3–2.7	I _{OH} = -100μA	V _{CCB} -0.2		V
			1.65–1.95	2.3	I _{OH} =6mA	1.25		
V _{OLA}	Low Level Output	Voltage	1.65–1.95	2.3–2.7	I _{OL} = 100μA		0.2	V
			1.65	2.3–2.7	I _{OL} = 18mA		0.6	
V _{OLB}	Low Level Output Voltage		1.65–1.95	2.3–2.7	I _{OL} = 100μA		0.2	V
			1.65–1.95	2.3	I _{OL} = 6mA		0.3	
Ι _Ι	Input Leakage Current @ OE, T/R		1.65–1.95	2.3–2.7	$0V \le V_I \le 3.6V$		±5.0	μA
I _{OZ}	3-STATE Output Leakage		1.65–1.95	2.3–2.7	$\label{eq:V_O} \begin{split} &0V \leq V_O \leq 3.6V, \\ &\overline{OE} = V_{CCB}, \\ &V_I = V_{IH} \text{ or } V_{IL} \end{split}$		±10	μA
I _{OFF}	Power Off Leakag	e Current	0	0	$0 \leq (V_I, V_O) \leq 3.6V$		10	μA
I _{CCA} /I _{CCB}			1.65–1.95	2.3–2.7	$A_n = V_{CCA}$ or GND, B_n , \overline{OE} , & $T/\overline{R} = V_{CCB}$ or GND		20	μA
			1.65–1.95	2.3–2.7	$\begin{split} & V_{CCA} \leq An \leq 3.6V, \\ & V_{CCB} \leq B_n, \ \overline{OE}, \\ & T/\overline{R} \leq 3.6V \end{split}$		±20	μA
ΔI_{CC}	Increase in I _{CC} pe T/R, OE	r Input, B _n ,	1.65–1.95	2.3–2.7	$V_{I} = V_{CCB} - 0.6V$		750	μA
	Increase in I _{CC} pe	r Input, A _n	1.65–1.95	2.3–2.7	$V_{I} = V_{CCA} - 0.6V$		750	μA

Symbol	Paramo	eter	V _{CCB} (V)	V _{CCA} (V)	Conditions	Min.	Max.	Units
V _{IHA}	HIGH Level Input	A _n	1.65–1.95	3.0–3.6		2.0		V
V _{IHB}	Voltage	B _n , T/ R , OE	1.65–1.95	3.0–3.6		0.65 x V _{CCB}		V
V _{ILA}	LOW Level Input	A _n	1.65–1.95	3.0–3.6			0.8	V
V _{ILB}	Voltage	$B_n, T/\overline{R}, \overline{OE}$	1.65–1.95	3.0–3.6			0.35 x V _{CCB}	V
V _{OHA}	HIGH Level Outpu	t Voltage	1.65–1.95	3.0–3.6	I _{OH} = -100μA	V _{CCA} -0.2		V
			1.65	3.0–3.6	I _{OH} = -24mA	2.2		
V _{OHB}	HIGH Level Outpu	t Voltage	1.65–1.95	3.0–3.6	I _{OH} = -100μA	V _{CCA} -0.2		V
			1.65–1.95	3.0	I _{OH} =6mA	1.25		
V _{OLA}	LOW Level Output	Voltage	1.65–1.95	3.0–3.6	I _{OL} = 100μA		0.2	V
			1.65	3.0–3.6	I _{OL} = 24mA		0.55	
V _{OLB}	LOW Level Output Voltage		1.65–1.95	3.0–3.6	Ι _{ΟL} = 100μΑ		0.2	V
			1.65–1.95	3.0	I _{OL} = 6mA		0.3	
I	Input Leakage Current @ OE, T/R		1.65–1.95	3.0–3.6	$0V \le V_I \le 3.6V$		±5.0	μA
I _{OZ}	3-STATE Output Leakage		1.65–1.95	3.0–3.6	$\begin{array}{l} 0V \leq V_O \leq 3.6V, \\ \overline{OE} = V_{CCB}, \\ V_I = V_{IH} \text{ or } V_{IL} \end{array}$		±10	μA
I _{OFF}	Power OFF Leaka	ge Current	0	0	$0 \le (V_I, V_O) \le 3.6V$		10	μA
I _{CCA} /I _{CCB}			1.65–1.95	3.0–3.6	$A_n = V_{CCA}$ or GND, B_n , \overline{OE} , & T/ $\overline{R} = V_{CCB}$ or GND		20	μA
		$ \begin{array}{ c c c c c c } 1.65-1.95 & 3.0-3.6 & V_{CCA} \leq A_n \leq 3.6V, & & \pm 20\\ & V_{CCB} \leq B_n, \ \overline{OE}, & & \\ & T/\overline{R} \leq 3.6V & & \\ \end{array} $	±20	μA				
ΔI_{CC}	Increase in I_{CC} per T/ \overline{R} , \overline{OE} ,	· Input, B _n ,	1.65–1.95	3.0–3.6	$V_{I} = V_{CCB} - 0.6V$		750	μA
	Increase in I _{CC} per	· Input, A _n	1.65–1.95	3.0–3.6	$V_{I} = V_{CCA} - 0.6V$		750	μA

Symbol	Parame	eter	V _{CCB} (V)	V _{CCA} (V)	Conditions	Min.	Max.	Units
V _{IHA}	HIGH Level Input	A _n	2.3–2.7	3.0–3.6		2.0		V
V _{IHB}	Voltage	B _n , T/R, OE	2.3–2.7	3.0–3.6		1.6		V
V _{ILA}	LOW Level Input	A _n	2.3–2.7	3.0–3.6			0.8	V
V _{ILB}	Voltage	$B_n, T/\overline{R}, \overline{OE}$	2.3–2.7	3.0–3.6			0.7	V
V _{OHA}	HIGH Level Output	t Voltage	2.3–2.7	3.0–3.6	I _{OH} = -100μA	V _{CCA} - 0.2		V
			2.3	3.0–3.6	I _{OH} = -24mA	2.2		1
V _{OHB}	HIGH Level Output	t Voltage	2.3–2.7	3.0–3.6	I _{OH} = -100μA	V _{CCB} - 0.2		V
			2.3–2.7	3.0	I _{OH} =18mA	1.7		1
V _{OLA}	LOW Level Output	Voltage	2.3–2.7	3.0–3.6	I _{OL} = 100μA		0.2 V	V
			2.3	3.0–3.6	I _{OL} = 24mA		0.55	1
V _{OLB}	LOW Level Output Voltage		2.3–2.7	3.0–3.6	I _{OL} = 100μA		0.2	V
			2.3–2.7	3.0	I _{OL} = 18mA		0.6	7
I	Input Leakage Current @ OE, T/R		2.3–2.7	3.0–3.6	$0V \le V_I \le 3.6V$		±5.0	μA
I _{OZ}	3-STATE Output Leakage @ A _n		2.3–2.7	3.0–3.6	$\begin{array}{l} 0V \leq V_O \leq 3.6V,\\ \overline{OE} = V_{CCA},\\ V_I = V_{IH} \text{ or } V_{IL} \end{array}$		±10	μA
I _{OFF}	Power OFF Leakag	ge Current	0	0	$0 \le (V_{I}, V_{O}) \le 3.6V$		10	μA
I _{CCA} /I _{CCB}			2.3–2.7	3.0–3.6	$A_n = V_{CCA} \text{ or GND,} \\ B_n, \overline{OE}, \& T/\overline{R} = V_{CCB} \\ \text{or GND}$		20	μA
		2.3–2.7	3.0–3.6	$\begin{split} & V_{CCA} \leq A_n \leq 3.6V, \\ & V_{CCB} \leq B_n, \ \overline{OE}, \\ & T/\overline{R} \leq 3.6V \end{split}$		±20	μΑ	
ΔI_{CC}	Increase in I _{CC} per T/R, OE	· Input, B _n ,	2.3–2.7	3.0–3.6	$V_{I} = V_{CCB} - 0.6V$		750	μA
	Increase in I _{CC} per	· Input, A _n	2.3–2.7	3.0–3.6	$V_{\rm I} = V_{\rm CCA} - 0.6V$		750	μA

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AC Electrical Characteristics

			T _A = –40°C to +85°C, C _L = 30 pF, R _L = 500 Ω						
			$\label{eq:V_CCB} \begin{split} V_{CCB} &= 1.65 \text{V to } 1.95 \text{V}, \\ V_{CCA} &= 2.3 \text{V to } 2.7 \text{V} \end{split}$		5V to 1.95V, 0V to 3.6V	$\label{eq:V_CCB} \begin{array}{l} V_{CCB} = 2.3 V \text{ to } 2.7 V, \\ V_{CCA} = 3.0 V \text{ to } 3.6 V \end{array}$		1	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Units	
t _{PHL} , t _{PLH}	Propagation Delay, A to B	1.5	5.8	1.5	6.2	0.8	4.4	ns	
t _{PHL} , t _{PLH}	Propagation Delay, B to A	0.8	5.5	0.6	5.1	0.6	4.0	ns	
t _{PZL} , t _{PZH}	Output Enable Time, OE to B	1.5	8.3	1.5	8.2	0.8	4.6	ns	
t _{PZL} , t _{PZH}	Output Enable Time, OE to A	0.8	5.3	0.6	5.1	0.6	4.0	ns	
t _{PLZ} , t _{PHZ}	Output Disable Time, OE to B	0.8	4.6	0.8	4.5	0.8	4.4	ns	
t _{PLZ} , t _{PHZ}	Output Disable Time, OE to A	0.8	5.2	0.6	5.6	0.6	4.8	ns	
t _{osHL} , t _{osLH}	Output to Output Skew ⁽⁷⁾		0.05		0.5		0.75	ns	

Note:

 Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{osHL}) or LOW-to-HIGH (t_{osLH}).

Dynamic Switching Characteristics

Symbol	Parameter	V _{CCB} (V)	V _{CCA} (V)	Conditions	T _A = +25°C Typical	Units
V _{OLP}	Quiet Output Dynamic	1.8	2.5	$C_L = 30 \text{ pF}, V_{IH} = V_{CC},$	0.25	V
	Peak V _{OL} , A to B	1.8	3.3	$V_{IL} = 0V$	0.25	1
		2.5	3.3		0.6	1
V _{OLP}	Quiet Output Dynamic	1.8	2.5	$C_{L} = 30 \text{ pF}, V_{IH} = V_{CC},$	0.6	V
	Peak V _{OL} , B to A	1.8	3.3	$V_{IL} = 0V$	0.8	
		2.5	3.3		0.8	1
V _{OLV}	Quiet Output Dynamic	1.8		$C_{L} = 30 \text{ pF}, V_{IH} = V_{CC},$	-0.25	V
	Valley V _{OL} , A to B	1.8	3.3	$V_{IL} = 0V$	-0.25	
		2.5	3.3		-0.6	
V _{OLV}	Quiet Output Dynamic	1.8	2.5	$C_{L} = 30 \text{ pF}, V_{IH} = V_{CC},$	-0.6	V
	Valley V _{OL} , B to A	1.8	3.3	$V_{IL} = 0V$	-0.8	1
		2.5	3.3		-0.8	
V _{OHV}	Quiet Output Dynamic	1.8	2.5	$C_L = 30 \text{ pF}, V_{IH} = V_{CC},$	1.3	V
	Valley V _{OH} , A to B	1.8	3.3	$V_{IL} = 0V$	1.3	1
		2.5	3.3		1.7	
V _{OHV}	Quiet Output Dynamic	1.8	2.5	$C_L = 30 \text{ pF}, V_{IH} = V_{CC},$	1.7	V
	Valley V _{OH} , B to A	1.8	3.3	$V_{IL} = 0V$	2.0]
		2.5	3.3		2.0]

74VCX163245
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-Bit Dual Supp
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h 3-STATE Outpu

Test OPEN t_{PLH}, t_{PHL} 6V at V_{CC} = 3.3 ±0.3V; t_{PZL}, t_{PLZ} $V_{CC} \ge 2$ at $V_{CC} = 2.5 \pm 0.2V$; 1.8V ± 0.15V

 $t_{\mathsf{PZH}},\,t_{\mathsf{PHZ}}$

Capacitance

Parameter

Input Capacitance

AC Loading and Waveforms

TEST C

SIGNAL C

Input/Output Capacitance

Power Dissipation Capacitance

V_{CC}

DUT

Switch

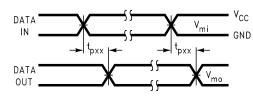
30 pF

Symbol

CIN

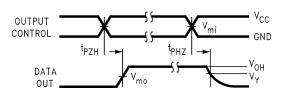
C_{I/O}

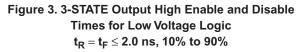
C_{PD}

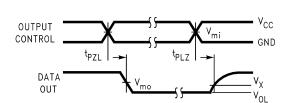


GND

Figure 2. Waveform for Inverting and Non-inverting Functions $t_{\text{R}} = t_{\text{F}} \leq 2.0$ ns, 10% to 90%







6.0V or V_{CC} * 2 t_{PZL} , t_{PLZ}

 $T_A = +25^{\circ}C$

5

6

20

t_{PLH}, t_{PHL}

t_{PZH}, t_{PHZ}

Units

pF

pF

pF

Conditions

 $V_{CCB} = 2.5V, V_{CCA} = 3.3V, V_{I} = 0V$

 $V_{CCB} = 2.5V, V_{CCA} = 3.3V, V_{I} = 0V$

O- OPEN

- GND

 $V_{CCB} = 2.5V, V_{CCA} = 3.3V,$

500Ω

500Ω

Figure 1. AC Test Circuit

 $V_I = 0V \text{ or } V_{CCA/B}, f = 10MHz$

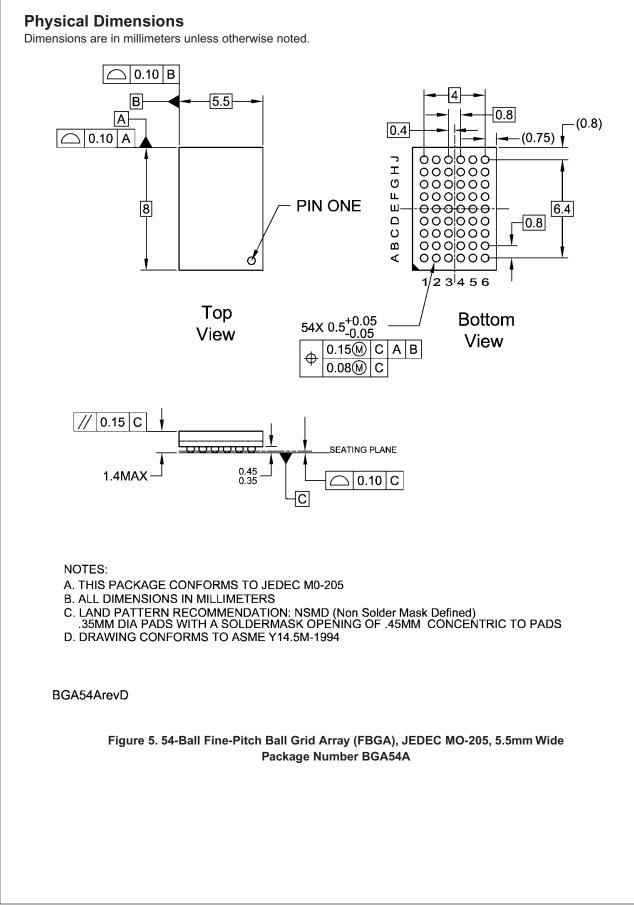
or V_{CCA/B}

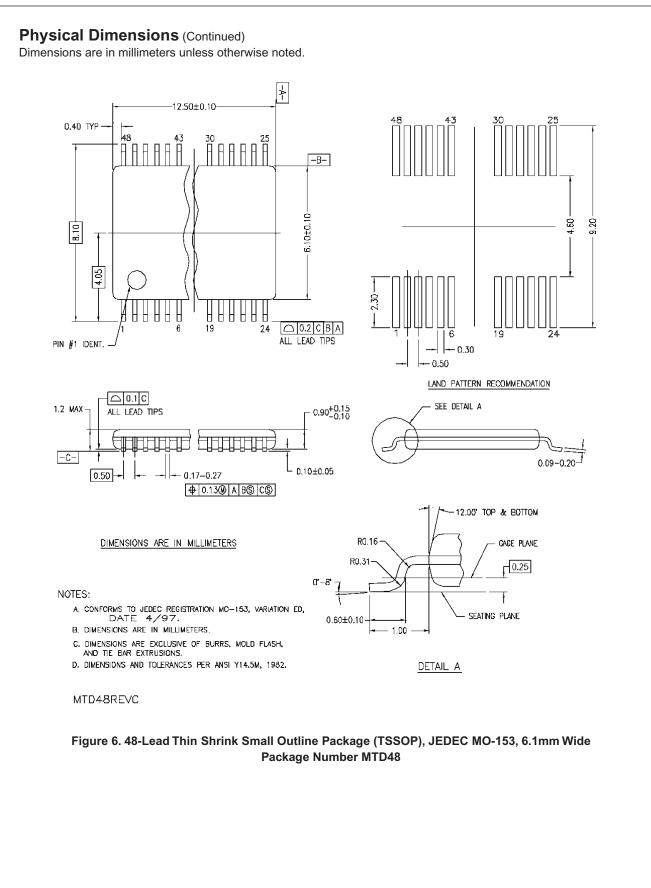
or V_{CCA/B}

Figure 4. 3-STATE Output Low Enable and Disable **Times for Low Voltage Logic** $t_R = t_F \leq$ 2.0 ns, 10% to 90%

	V _{CC}		
Symbol	3.3V ± 0.3V	2.5V ± 0.2V	1.8V ± 0.15V
V _{mi}	1.5V	V _{CC} / 2	V _{CC} / 2
V _{mo}	1.5V	V _{CC} / 2	V _{CC} / 2
V _X	V _{OL} + 0.3V	V _{OL} + 0.15V	V _{OL} + 0.15V
V _Y	V _{OH} – 0.3V	V _{OH} – 0.15V	V _{OH} – 0.15V

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